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Title:Spectrally wide-band terahertz wave modulator based on optically tuned graphene

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Abstract:New applications in the realms of terahertz (THz) technology require versatile adaptive optics and powerful modulation techniques. Semiconductors have proven to provide fast all-optical terahertz wave modulation over a wide frequency band. We show that the attenuation and modulation depth in optically driven silicon modulators can be significantly enhanced by deposition of graphene on silicon (GOS). We observed a wide-band tunability of the THz transmission in a frequency range from 0.2 to 2 THz and a maximum modulation depth of 99%. The maximum difference between the transmission through silicon and GOS is  $\Delta t = 0.18$  at a low photodoping power of 40 mW. At higher modulation power, the enhancement decreased due to charge carrier saturation. We developed a semianalytical band structure model of the graphene-silicon interface to describe the observed attenuation and modulation depth in GOS.   
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